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June 2017

# FAN54110 USB-Compatible Single-Cell Li-Ion Linear Charger with DBP

#### **Features**

Fully Integrated, High-Efficiency Charger for Single-Cell Li-Ion and Li-Polymer Battery Packs

Charge Voltage Accuracy: ±0.5% at 25°C

±1% from -30 to 85°C

+0/-10% Charge Current Regulation Accuracy

28 V Absolute Maximum Input Voltage

1 A Maximum Charge Current

Support for Dead Battery Provision (DBP) of USB Battery Charging Specification 1.2

Programmable through I<sup>2</sup>C Interface with Fast Mode (400 kHz) Compatibility

- Input Current
- Fast-Charge / Termination Current
- Charger Voltage

Safety Timer with Reset Control

Weak Input Sources Accommodated by Reducing Charging Current to Maintain Minimum  $V_{\text{BUS}}$  Voltage

Low Reverse Leakage to Prevent Battery Drain to VBUS

# **Applications**

**Smart Phones** 

**Tablets** 

Portable Media Players

Li Ion Powered Devices

# **Description**

The FAN54110 is a USB-compatible single-cell, linear Li-lon charger with support for Dead Battery Provision (DBP).

The device employs Over-Voltage Protection (OVP) circuitry to protect the device, load, and battery. The maximum charge current is rated at 1 A and can be programmed from 100 mA to 1 A through the I<sup>2</sup>C interface, optimizing charging for various battery sizes.

Dynamic Input Voltage Control ensures weak power sources can be used to power the FAN54110 without collapsing to an unusable input voltage for charging.

Open-drain status pins, STAT and POK\_B, provide a status of charging and input power. The STAT pin also notifies the system processor when an I<sup>2</sup>C interrupt occurs so the processor can take action based on the interrupt.

The FAN54110 conforms to the constraints of the Dead Battery Provision within the BC1.2 specification, including a 30-minute timer that cannot exceed 45 minutes.

The FAN54110 is designed to be stable with space-saving ceramic capacitors. The FAN54110 is available in a 15-bump, 0.4 mm pitch, WLCSP package.

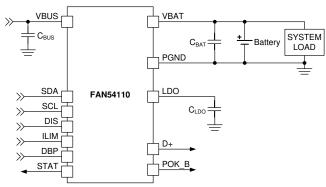


Figure 1. Typical Application

# **Ordering Information**

Part Number	PN Reg00h[4:3]	Temperature Range Package		Packing Method
FAN54110UCX	00	-40°C to 85°C	15-Bump, Wafer-Level Chip-Scale (WLCSP), 0.4 mm Pitch	Tape and Reel

#### **Recommended External Components**

Component	Description	Vendor	Parameter	Min.	Typ.(1)	Unit
C <sub>BUS</sub>	1.0 μF, 10%, 25 V, X5R, 0603	Murata GRM188R61E105K TDK C1608X5R1E105M	С	0.5	1.0	μF
C <sub>BAT</sub> <sup>(2)</sup>	4.7 μF, 10%, 6.3 V, X5R, 0603	Murata GRM188R60J475K TDK C1608X5R0J475K	С	2.0	4.7	μF
C <sub>LDO</sub>	1.0 μF, 10%, 6.3 V, X5R, 0402	Murata GRM155R60J105M	С	0.4	1.0	μF

#### Notes:

- 1. Does not reflect effects of bias, tolerance, and temperature.
- 2.  $C_{BAT}$  is placed as close to the charger IC as possible. A minimum requirement of 30  $\mu$ F distributed system capacitance ( $C_{SYS}$ ) is parallel with  $C_{BAT}$ , but can be located further from the IC.

# **Block Diagram**

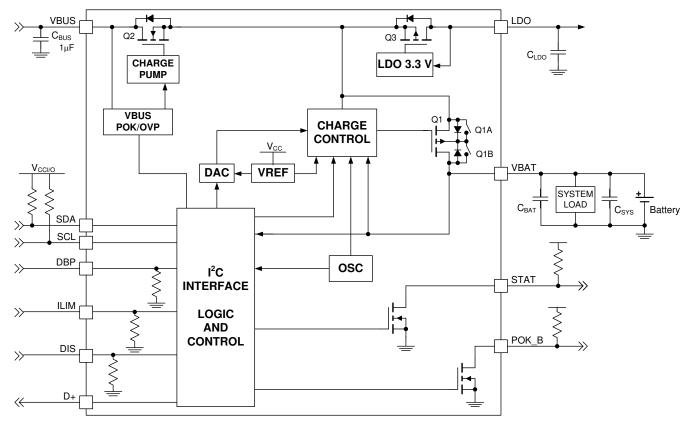
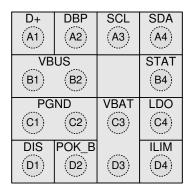
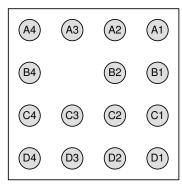


Figure 2. IC and System Block Diagram



**Top View** 



**Bottom View** 

## **Pin Definitions**

Pin#	Name	Description
A1	D+	Connect to the USB connector D+ pin
AT D+		Charger IC sources 0.6 V in CHARGE state when DBP is LOW. Otherwise, this pin is 3-state.
A2 DBP		Dead Battery Provision Disable
7 12	<i>DD</i> 1	Pull HIGH to disable charger D+ output. Internal pull-down resistor.
A3	SCL	I <sup>2</sup> C Interface Serial Clock
A4	SDA	I <sup>2</sup> C Interface Serial Data
B1, B2	VBUS	Charger Input Voltage
61, 62	VB03	Bypass with a 1 μF capacitor directly to PGND.
		Status / Interrupt
B4 STAT		Open-drain output indicating charge status. The IC pulls this pin LOW when charge is in process. High impedance when charging is done or charger is disabled. Also used as system interrupt. 128 µs pulse and then high impedance indicates to the system a fault has occurred.
C1, C2	PGND	Power Ground
G1, G2   FGIND		Power return for gate drive and power transistors.
C4	LDO	3.3 V LDO
04	LDO	3.3 V regulator output.
D1	DIS	Active-High Disable
	D10	When pulled HIGH, the charger is disabled. Internal pull-down resistor.
		VBUS Power-OK Monitor
D2 POK_B		Open-drain output that is pulled LOW when $V_{\text{BUS}}$ is greater than the $V_{\text{BUS}}$ validation threshold and lower than $V_{\text{BUS}}$ OVP. High impedance when outside this range.
		Battery Voltage
C3, D3	VBAT	Connect to the positive (+) terminal of the battery pack. Bypass locally with a 4.7 $\mu\text{F}$ capacitor to PGND.
D4	ILIM	Input Current Limit
D4	ILIIVI	This pin sets the input current limit for t <sub>30MIN</sub> charging. Internal pull-down resistor.

# **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol		Parameter		Max.	Unit
V <sub>BUS</sub>	Voltage on VBUS	Continuous	-1.2	28.0	V
V <sub>BAT</sub>	Voltage on VBAT		-0.3	6.5	V
Vo	Voltage on Other Pins		-0.3	(3)	V
	Electrostatic Discharge Protection Level	Human Body Model per ANSI/ESDA/JEDEC JS-001-2012 (All Pins)	2000		
ESD		Charged Device Model per JESD22-C101 (All Pins)	15	00	V
		IEC 61000-4-2 System (VBUS and D+ Pins)	80	00	
LU	Latch Up	JESD78 - Class 1, 25°C	±1	00	mA
TJ	Junction Temperature		-40	+150	°C
T <sub>STG</sub>	Storage Temperature		-65	+150	°C
TL	Lead Soldering Temper	ature, 10 Seconds		+260	°C

#### Note:

Lesser of 6.5 V or V<sub>BAT</sub> + 0.3 V.

# **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit
V <sub>IN</sub>	Supply Voltage	4	6	V
T <sub>A</sub>	Ambient Temperature	-30	+85	°C
TJ	Junction Temperature	-30	+125	°C

# **Thermal Properties**

Junction-to-ambient thermal resistance is a function of application and board layout. This data is measured with four-layer 2s2p boards in accordance to JEDEC standard JESD51. Special attention must be paid not to exceed junction temperature  $T_{J(max)}$  at a given ambient temperature  $T_{A}$ . For measured data, see the Evaluation Board Measured  $\theta JA$  table.

Symbol	mbol Parameter		Unit
$\theta$ JA	Junction-to-Ambient Thermal Resistance		°C/W
θ <sub>JB</sub> Junction-to-PCB Thermal Resistance 20		20	°C/W

# **Electrical Specifications**

Unless otherwise specified: circuit of Figure 2, recommended operating temperature range for  $T_J$  and  $T_A$ ,  $V_{BUS}=5.0$  V, DIS=0 (Charger Mode operation), SCL, SDA=0 or 1.8 V; typical values are for  $T_J=25^{\circ}$ C.

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Unit
Power Su	ipplies	1				•	
V <sub>IN(MIN)1</sub>	V <sub>BUS</sub> Input Voltage Rising	To Initiate and Pass VBU	JS Validation	4.18	4.40	4.65	V
V <sub>IN(MIN)2</sub>	Minimum V <sub>BUS</sub> during Charge	VBUS Regulation Loop is	s Off	2.95	3.10	3.35	V
tvbus_valii	V <sub>BUS</sub> Validation Time				32		ms
V <sub>BUS_REF</sub>	V <sub>BUS</sub> Regulation Loop Threshold	Relative to VBUS_REF S	Setting	-5		+5	%
I <sub>VBUS</sub>	V <sub>BUS</sub> Current	DIS=1			890	1,000	μА
I <sub>DIS</sub>	V <sub>BUS</sub> Discharge Current	VBUS Removal or Valida	ation	40	63	90	mA
	Battery Discharge Current during	V <sub>BAT</sub> =4. 2 V, VBUS=Oper No I <sup>2</sup> C Traffic, -30°C < T <sub>o</sub>			5	10	
I <sub>BAT</sub>	SLEEP State	V <sub>BAT</sub> =4. 2 V, VBUS=Open, SDA=SCL=0 V, -30°C < T <sub>J</sub> < 85°C			3	8	μΑ
I <sub>BUS_LKG</sub>	VBAT to VBUS Leakage Current	V <sub>BAT</sub> =4. 2 V, V <sub>BUS</sub> =0 V, -3	30°C < T <sub>J</sub> < 85°C		<1	2	μΑ
Charger \	Voltage Regulation			•			
	Charge Voltage Range			3.38		4.44	V
	Charge Voltage Accuracy	V <sub>OREG</sub> =4. 2 V	T <sub>J</sub> =25°C	-0.5		+0.5	- %
.,			-30°C < T <sub>J</sub> < 85°C	-1		+1	
$V_{OREG}$		3.38 V < V <sub>OREG</sub> < 4.44 V	T <sub>J</sub> =25°C	-1		+1	
			-30°C < T <sub>J</sub> < 85°C	-1.5		-1.5	
	V <sub>BAT</sub> Overshoot Pulsed Load <sup>(4)</sup>	See V <sub>BAT</sub> Overshoot Test			2	10	mV
Fast Cha	rging Current Regulation						
	Output Charge Current Range			100		1,000	mA
<b>I</b> OCHRG	Charge Current Accuracy	I <sub>OCHRG</sub> ≥ 350 mA		-10	-5	0	%
	(measured at $V_{BUS}$ , includes $I_{CHRG} + I_{REG}$ )	lochrg < 350 mA		-15	-7	0	76
Logic Lev	vels: DIS, SDA, SCL, ILIM, DBP						
V <sub>IH</sub>	High-Level Input Voltage			1.05			V
$V_{IL}$	Low-Level Input Voltage					0.4	V
I <sub>IN</sub>	Input Bias Current	Input Tied to GND or Greater of V <sub>BAT</sub> or Valid V <sub>BUS</sub>			0.01	1.00	μА
R <sub>PD</sub>	ILIM, DBP, DIS Pull-Down Resistance			0.6	0.9	1.4	МΩ

#### **VBAT Overshoot Test**

In the figure below, Iocharge=1 A (1111), Voreg=4.2 V. ILOAD tref=1  $\mu$ s. Charge current prior to load transient=  $\frac{20mV}{200m\Omega}$  = 100mA

Overshoot is measured as the peak voltage above  $V_{BAT}$  level prior to the load transient application.  $C_{SYS}$  represents the distributed system capacitance across the VBAT terminals and is assumed to be a minimum of 30  $\mu$ F.

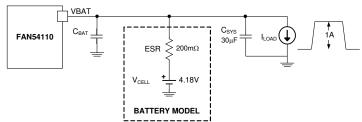


Figure 3. VBAT Overshoot Test Condition

# **Electrical Specifications**

Unless otherwise specified: circuit of Figure 2, recommended operating temperature range for  $T_J$  and  $T_A$ ,  $V_{BUS}$ =5.0 V, DIS=0 (Charger Mode operation), SCL, SDA=0 or 1.8 V; typical values are for  $T_J$ =25°C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Charge Te	rmination Detection					
-	Termination Current Range	VBAT > VOREG - VRCH, VBUS > VBUS_REF	20		170	mA
I <sub>TERM</sub>	T : :: 0	Iterm > 80 mA	-10		+10	0/
	Termination Current Accuracy	I <sub>TERM</sub> ≤ 80 mA	-20		+20	%
Battery Re	charge Threshold		•			
$V_{RCH}$	Recharge Threshold	V <sub>BAT</sub> Falling by V <sub>RCH</sub> below V <sub>OREG</sub> Threshold		100		mV
3. 3 V Line	ar Regulator		•			
$V_{REG}$	3.3 V Regulator Output	I <sub>REG</sub> from 0 to 40 mA	3.10	3.30	3.50	V
DBP Outpu	ut				•	
V <sub>DBP_SRC</sub>	Voltage on D+ pin	DBP=0, I <sub>LOAD</sub> on D+ from 0 to 250 μA	0.51	0.60	0.69	V
I <sub>DBP_OFF</sub>	Leakage Current	DBP=1, V <sub>D+</sub> from 0 to 3. 6 V	-1		+1	μΑ
STAT / PO	K_B Output		•			
V <sub>OL</sub>	STAT / POK_B Output Low	I=10 mA			0.4	٧
Іон	STAT / POK_B Leakage Current	V=5 V			1	μΑ
Battery De	tection		•			
IDETECT	Battery Detection Current before Charge Done (Sink Current)	Begins after Termination Detected		-1		mA
t <sub>DETECT</sub>	Battery Detection Time			262		ms
Power Swi	tches (see Error! Reference source	e not found.)			I	
Q1 R <sub>DS(ON)</sub>	Q1 On Resistance			175	260	mΩ
Q2 R <sub>DS(ON)</sub>	Q2 On Resistance			110	170	mΩ
Protection	and Timers			I	I	
\	V <sub>BUS</sub> OVP Accuracy	V <sub>BUS</sub> Rising	-7		+7	%
VBUSOVP	Hysteresis	V <sub>BUS</sub> Falling		100		mV
	Battery Short-Circuit Threshold	V <sub>BAT</sub> Rising	2.10	2.27	2.40	٧
V <sub>SHORT</sub>	Hysteresis	V <sub>BAT</sub> Falling		120		mV
I <sub>SHORT</sub>	Linear Charging Current	V <sub>BAT</sub> < V <sub>SHORT</sub>	85	93	100	mA
I <sub>LIM(PTM)</sub>	Production Test Mode Current Limit		2.2			Α
_	Thermal Shutdown Threshold <sup>(4)</sup>	T <sub>J</sub> Rising	130	145	160	
T <sub>SHUTDWN</sub>	Re-Enable Threshold <sup>(4)</sup>	T <sub>J</sub> Falling		T <sub>CF</sub>		°C
T <sub>CF</sub>	Thermal Regulation Accuracy <sup>(4)</sup>	Relative to T <sub>CF</sub> Setting	-10		+10	°C
<b>t</b> 32S	32-Second Timer		20.5	24.3	28.0	S
tзомім	30-Minute Timer		30	38	45	min
tosc	125 kHz Oscillator Tolerance	Timing in all Sequencing Diagrams	-15		15	%

## Note:

4. Guaranteed by design; not tested in production.

# I<sup>2</sup>C Timing Specifications

Guaranteed by design.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Uni
		Standard Mode			100	
	SCI Clark Francisco	Fast Mode			400	1.11_
fscl	SCL Clock Frequency	High-Speed Mode, C <sub>B</sub> ≤ 100 pF			3400	kH
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF			1700	
	Bus-Free Time between STOP	Standard Mode		4.7		
tBUF	and START Conditions	Fast Mode		1.3		μS
		Standard Mode		4		μS
thd;sta	START or Repeated START Hold Time	Fast Mode		600		
	Hold Time	High-Speed Mode		160		ns
		Standard Mode		4.7		
		Fast Mode		1.3		μS
tLOW	SCL LOW Period	High-Speed Mode, C <sub>B</sub> ≤ 100 pF		160		
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF		320		ns
		Standard Mode		4		μ
		Fast Mode		600		ns
thigh	SCL HIGH Period	High-Speed Mode, C <sub>B</sub> ≤ 100 pF		60		
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF		120		
		Standard Mode		4.7		μ
tsu:sta	Repeated START Setup Time	Fast Mode		600		μ
130,31A		High-Speed Mode		160		n
		Standard Mode		250		
tsu:dat	Data Setup Time	Fast Mode		100		n
t50;DAT	Data Setup Time	High-Speed Mode		100		'''
		Standard Mode	0	10	3.45	
		Fast Mode				μ
$t_{\text{HD};\text{DAT}}$	Data Hold Time		0		900 70	۰
		High-Speed Mode, C <sub>B</sub> ≤ 100 pF				n
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF  Standard Mode	0	10	150	
				).1C <sub>B</sub>	1000	
trcL	SCL Rise Time	Fast Mode	20+0	).1C <sub>B</sub>	300	n
		High-Speed Mode, C <sub>B</sub> ≤ 100 pF		10	80	
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF	00.0	20	160	
		Standard Mode		).1C <sub>B</sub>	300	
t <sub>FCL</sub>	SCL Fall Time	Fast Mode	20+0	).1C <sub>B</sub>	300	n
		High-Speed Mode, C <sub>B</sub> ≤ 100 pF		10	40	
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF	20.	20	80	
	SDA Rise Time	Standard Mode		).1C <sub>B</sub>	1000	
trda	Rise Time of SCL after a	Fast Mode	20+0	).1C <sub>B</sub>	300	ns
trcL1	Repeated START Condition and after ACK Bit	High-Speed Mode, C <sub>B</sub> ≤ 100 pF		10	80	-
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF		20	160	<u></u>

Continued on the following page...

# I<sup>2</sup>C Timing Specifications

Guaranteed by design.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
	SDA Fall Time	Standard Mode	20+0	).1C <sub>B</sub>	300		
		Fast Mode	20+0	20+0.1C <sub>B</sub> 300			
t <sub>FDA</sub>		High-Speed Mode, C <sub>B</sub> ≤ 100 pF		10	80	ns	
		High-Speed Mode, C <sub>B</sub> ≤ 400 pF		20	160		
		Standard Mode		4		μS	
tsu;sто	Stop Condition Setup Time	Fast Mode		600			
		High-Speed Mode		160		ns	
Св	Capacitive Load for SDA, SCL				400	pF	

# **Timing Diagram**

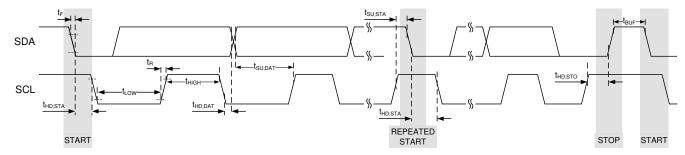
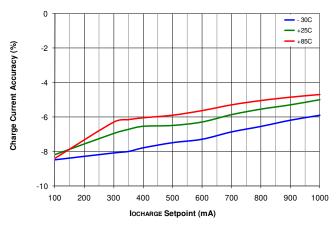


Figure 4. I<sup>2</sup>C Interface Timing for Fast and Slow Modes

# **Typical Characteristics**

Unless otherwise specified; circuit of Figure 2, V<sub>OREG</sub>=4.2 V, V<sub>BUS</sub>=5.0 V, and T<sub>A</sub>=25°C.



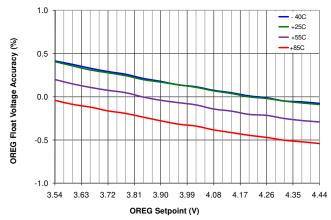
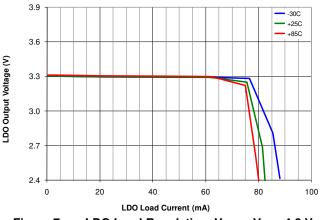


Figure 5. lochrg Accuracy Over-Temperature, 3.7 VBAT

Figure 6. OREG Accuracy Over-Temperature, I<sub>BAT</sub>=100 mA



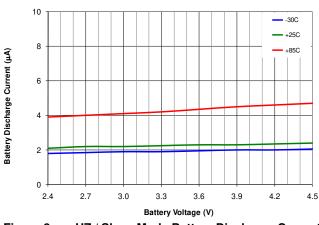
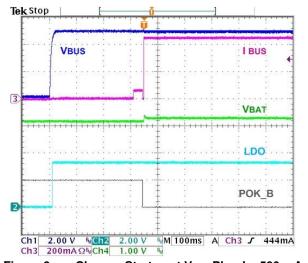


Figure 7. LDO Load Regulation, V<sub>OREG</sub>=V<sub>BAT</sub>=4.2 V

Figure 8. HZ / Sleep Mode Battery Discharge Current, V<sub>BUS</sub> Open, DIS=SDA=SCL=0 V



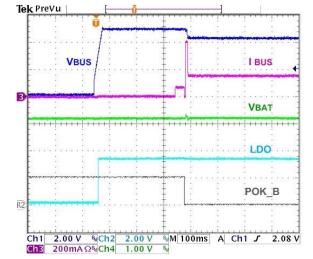


Figure 9. Charger Startup at V<sub>BUS</sub> Plug-In, 500 mA  $I_{OCHRG}$ , 3.2 V<sub>BAT</sub>, 1 k $\Omega$  LDO Load, ILIM=DBP=1.8 V

Figure 10. Charger Startup at VBUS Plug-In Using 150 mA Current Limited Source, 3.2 V<sub>BAT</sub>, 500 mA I<sub>OCHRG</sub>, 1 kΩ LDO Load, ILIM=DBP=1.8 V

## **Typical Characteristics**

Unless otherwise specified; circuit of Figure 2, V<sub>OREG</sub>=4.2 V, V<sub>BUS</sub>=5.0 V, and T<sub>A</sub>=25°C.

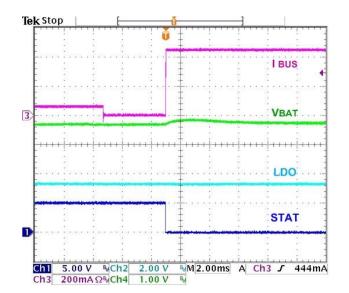
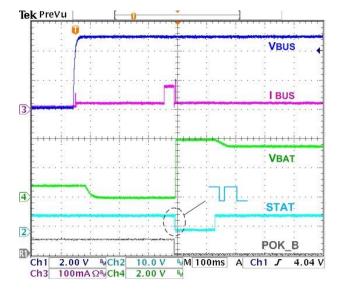


Figure 11. Charger Startup Using HZ Bit Reset, 3.7  $V_{BAT},\\500$  mA  $I_{OCHRG},$  1 k $\Omega$  LDO Load, ILIM=DBP=1.8 V

Figure 12. Charger Startup at  $V_{BUS}$  Plug-In with Dead Battery (Protection Switch Open), 1 k $\Omega$  LDO Load, ILIM=DBP=0 V



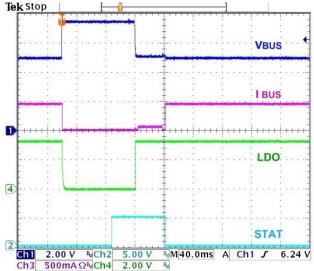
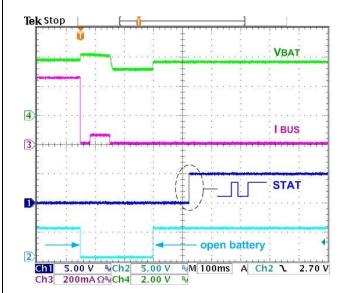


Figure 13. Charger Startup at  $V_{BUS}$  Plug-In with No Battery, 300  $\Omega$  LDO Load, ILIM=DBP=0 V

Figure 14. VBUS OVP Response while Charging, 3.7  $V_{BAT}$ , 500 mA  $I_{OCHRG}$ , 1 k $\Omega$  LDO Load, ILIM=DBP=1.8 V

## **Typical Characteristics**

Unless otherwise specified; circuit of Figure 2, V<sub>OREG</sub>=4.2 V, V<sub>BUS</sub>=5.0 V, and T<sub>A</sub>=25°C.



VBAT

I BUS

STAT

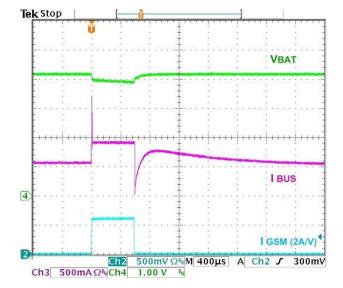
open battery

chi 5.00 V % Ch2 5.00 V % M 100ms A Ch2 \ 2.70 V Ch3 200mA Ω % Ch4 2.00 V %

Tek Stop

Figure 15. Battery Removal/Insertion while Charging, 3.7  $V_{BAT}$ , 500 mA  $I_{OCHRG}$ , ILIM=DBP=1.8 V, ITERM DIS=0

Figure 16. Battery Removal/Insertion while Charging, 3.7 VBAT, 500 mA IOCHRG, ILIM=DBP=1.8 V, ITERM\_DIS=1



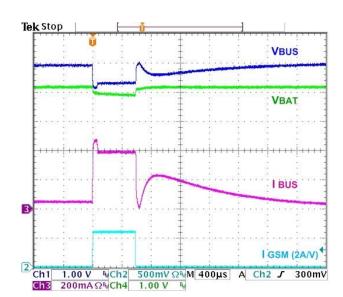


Figure 17. 1.2 A Load Pulse, t<sub>R</sub>=t<sub>F</sub>=5 μs, 4.19 V<sub>BAT</sub>, 1.0 A locheg

Figure 18. 1.2 A Load Pulse,  $t_R=t_F=5~\mu s$ , 500 mA Current Limited Source, 4.2  $V_{BAT}$ , 1.0  $A_{IOCHRG}$ , 4.32  $V_{BUS\_REF}$ 

## **Basic Operation**

The FAN54110 is a USB-compatible single-cell Li-lon charger with support for Dead Battery Provision (DBP) and a maximum charge current rated at 1 A.

The FAN54110 conforms to all the requirements for the DBP within the BC1. 2 specifications, including a 30-minute timer that cannot exceed 45 minutes.

The FAN54110 is designed to be stable with space-saving ceramic capacitors and is available in a 15-bump, 0.4 mm pitch, WLCSP.

## **Charger Circuit Details**

#### **VBUS Insertion**

When the IC detects that  $V_{BUS}$  has risen above  $V_{IN(MIN)1}$ , adapter validation and battery voltage detection will occur before charging begins. To pass validation,  $V_{BUS}$  must remain above  $V_{IN(MIN)1}$  and below  $V_{BUSOVP}$  for  $tv_{BUS\_VALID}$  before the IC initiates charging. Refer to Figure 20 and Figure 21 for details.

If  $V_{\text{BUS}}$  is validated, the POK\_B pin pulls LOW and an interrupt is issued to indicate to the system that VBUS is connected. This point is considered to be VBUS\_POR.

If VBUS fails validation, the POK\_B pin remains HIGH and an interrupt is issued. Re-validation is attempted every two seconds.

Setting the HZ\_MODE bit or DIS pin prevents validation from occurring after VBUS rises above V<sub>IN(MIN)1</sub>, but, VBUS validation will be performed prior to entering Charge State from any state where the charger is off.

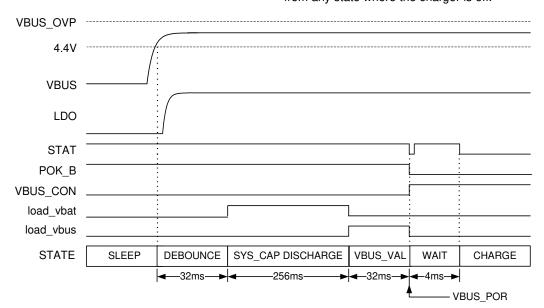


Figure 19. VBUS Plug-In Timing: DIS=0, HZ MODE=0, DBP=1

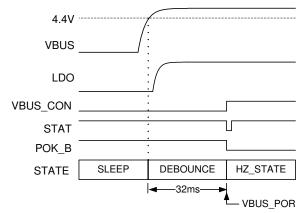


Figure 20. VBUS Plug-In Timing: DIS=1 or (DBP=1 and HZ\_MODE=1)

#### **VBUS POR and DBP Charging**

If the DBP pin is HIGH at VBUS\_POR, the IC operates in accordance with its  $I^2C$  register settings and starts the  $t_{32s}$  timer when charging begins. This is the normal operating mode for the FAN54110.

If the DBP pin is LOW at VBUS\_POR or the DBP pin transitions from HIGH to LOW when VBUS is valid, the FAN54110:

- Resets its registers to default values
- Charges with its charge current limit set by the state of the ILIM pin:
  - ILIM= LOW, I<sub>OCHRG</sub>=100 mA
  - ILIM= HIGH, I<sub>OCHRG</sub>=350 mA
- Starts the t<sub>30MIN</sub> timer
- Sources 0.6 V to the D+ pin

BC1.2 and USB 2.0 allow a portable device (defined as a device with a battery) with a dead battery to take a maximum of 100 mA from the USB VBUS line for a maximum of 45 minutes as long as the portable device forces the D+ line to 0.6 V typical.

Once DBP transitions from LOW to HIGH, D+ is three-stated and charge parameters may be programmed by the host. Charge current remains controlled by the state of the ILIM pin and the t<sub>30MIN</sub> timer continues running until the first I<sup>2</sup>C write occurs; at which time, charge current is controlled by the I<sub>OCHARGE</sub> (Reg03h[7:4]) bits and the timer changes to t<sub>32S</sub>.

The ILIM and DBP pins are internally pulled down and there is typically nothing to force them HIGH at this point due to the processor / system not yet being awake. When the t<sub>30MIN</sub> timer expires, the FAN54110 removes the 0.6 V from D+ and stops charging. The D+ pin is three-stated when DBP is HIGH.

#### **Battery Absent at VBUS Insertion**

Before charging begins, if  $V_{\text{BAT}}$  is below  $V_{\text{SHORT}}$ , the FAN54110 will determine whether the battery is absent or present.

To accomplish this, the IC temporarily raises  $V_{OREG}$  to 4.0 V after  $V_{BAT}$  has risen above  $V_{SHORT}$ . If  $V_{BAT}$  remains below 3.7 V for more than 128 ms, the battery is present. If  $V_{BAT}$  is above 3.7 V after 128 ms, the battery is assumed absent.

If battery absence is detected, all registers are reset to their default values, the NOBAT bit is set, and an interrupt is generated. Also, it is assumed the DBP pin is LOW since the system was without a power source prior to plug in. The FAN54110 will provide power to the system with STAT HIGH in DBP Mode until otherwise instructed through I<sup>2</sup>C commands. This allows the host processor an opportunity to detect charger type and negotiate with the USB host for higher current.

The IC continues to provide current, provided that:

- a timer (t<sub>30MIN</sub> or t<sub>32S</sub>) is running
- HZ MODE (Reg=01h[6])=0 and DIS=LOW.

The current drawn from VBUS is determined by either the state of ILIM pin or the  $I_{\text{OCHARGE}}$  programming.

#### **Charging Stages**

Figure 21 shows the different charging stages when a battery is present and discharged below 2.25 V.

PRE-CHARGE is when the battery voltage is below  $V_{SHORT}$  and a current of  $I_{SHORT}$  is used to charge the battery above VSHORT. This stage is typically used to recover a deeply discharge battery with its protection switch open.

CURRENT REGULATION increases charging current considerably above I<sub>SHORT</sub> to a programmable I<sub>OCHARGE</sub> (Reg 03h[7:4]) level.

VOLTAGE REGULATION occurs during charging when VBAT reaches VOREG (Reg4[5:0]). The current charging the battery is reduced, limited by the battery's ESR and its internal cell voltage.

- If ITERM\_DIS (Reg03h[0])=0, charging current decreases to ITERM (Reg03h[3:0]), where Charge Termination occurs.
- If ITERM\_DIS=1 (default configuration), charging will continue past ITERM until current decreases to 0A, where the part will remain in Charge Mode with the t32s timer running.

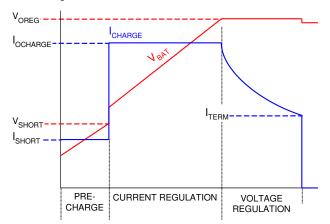


Figure 21. Typical Charge Profile

#### **Charge Termination**

During Voltage Regulation, charging continues until the  $I_{BAT} \leq I_{TERM}$ . If ITERM\_DIS=0, charging stops and the  $t_{328}$  timer continues counting. The STAT pin remains LOW until the IC determines whether the  $I_{BAT} < I_{TERM}$  condition was caused by VBUS removal, Battery Removal, or by the battery being fully charged (Charge Termination).

During Charge Termination, the  $t_{32S}$  timer will continue running, but, if it expires will not reset all registers until Recharge. Setting the TMR\_RST bit (Reg8[7]) during Charge Termination will reset the  $t_{32S}$  timer. Refer to the Timers section for more details.

#### **Recharge from Charge Termination**

During Charge Termination, if  $V_{\text{BAT}}$  falls by  $V_{\text{RCH}}$  below  $V_{\text{OREG}}$ , charging starts again.

A recharge condition de-bounce time of 60 ms is used to prevent transient battery load currents (such as GSM current pulses) from triggering auto-recharge unnecessarily.

#### **Battery Removal during Charging**

When ITERM\_DIS=0 and the charge current drops below the ITERM setting, a load current (IDETECT) is placed on VBAT in order to determine if the battery was removed during charging. If the battery is determined to be present, the load is removed, and Charge Done State is entered. If the battery is determined to be absent, the IC enters a fault state, which waits with the charger disabled for two seconds, then restarts the charger validation process.

- If the battery is determined to be present, the load is removed, and Charge Termination occurs.
- If the battery is determined to be absent, charging is disabled, all registers except ITERM\_DIS are reset to default values, the NOBAT interrupt bit is set, and the STAT pin rises. After 2s, the charger will restart validation and if the battery is re-inserted, the IC will return to Charge State.

In response to  $V_{BAT}$  collapsing, though, the system electronics have likely lowered the DBP pin which will reset all registers. As a result, the ITERM\_DIS bit will be reset to 1, which will set the unloaded VBAT pin to output 3.54V (the default  $V_{OREG}$  setting) and place the IC in Charge State with the NOBAT bit remaining set until the next VBUS\_POR validation.

#### **VBUS Removal and SLEEP**

When  $V_{BUS}$  falls below either  $V_{IN(MIN)2}$  or  $V_{BAT}$ , the IC ceases charging, the POK\_B pin sets HIGH, and an interrupt occurs to indicate to the system that VBUS has been removed. The IC then enters the Sleep State.

#### LDO

The FAN54110 provides a regulated 3.3 V LDO output when a valid  $V_{\text{BUS}}$  condition exists to power the USB PHY. Regulation occurs within 5 ms of valid  $V_{\text{BUS}}$  being applied.

LDO load current is derived from  $V_{\text{BUS}}$  and is subject to the  $I_{\text{OCHARGE}}$  setting / limit. Available battery charging current is reduced by the LDO load current.

# **Charger/Battery/System Protections**

#### **Timers**

There are two timers on the FAN54110; t<sub>328</sub> and the t<sub>30MIN</sub>.

The t<sub>32S</sub> timer is for normal operation where the DBP pin is HIGH. When charging begins after a VBUS\_POR with the DBP pin HIGH, the t<sub>32S</sub> timer is started. If the t<sub>32S</sub> timer is allowed to expire, charging ceases and the part will enter the IDLE State where all registers are reset. A write to any register can return the IC to charging. To avoid a t<sub>32S</sub> timer fault, the host must reset the timer by periodically setting the TMR\_RST (Reg08h[7]) bit before it expires.

The  $t_{30\text{MIN}}$  timer is for unattended charging. If  $V_{\text{BAT}} < V_{\text{SHORT}}$  the device is assumed to be dead and the DBP pin is, therefore, LOW. When charging begins after a VBUS\_POR with  $V_{\text{BAT}} < V_{\text{SHORT}}$  and the DBP pin LOW, the  $t_{30\text{MIN}}$  timer is started. If the  $t_{30\text{MIN}}$  timer is allowed to expire, charging

ceases and the part will enter the IDLE State where all registers are reset. Only a new VBUS\_POR will return the IC to charging.

During unattended charging, if the DBP pin transitions from LOW to HIGH (due to the host waking up and controlling the charger):

- 1- If VBAT<VSHORT, the t30MIN timer will continue running.
- 2- If VBAT>VSHORT, the t30MIN timer will continue running until the first I<sup>2</sup>C write. Then the t30MIN will stop and the t32S timer is started.

#### **VBUS Over-Voltage**

The FAN54110 contains programmable Over-Voltage Protection (OVP) on VBUS, ranging from 6.5 V to 8.0 V, as specified in the  $V_{\text{BUSOVP}}$  (Reg01h[2:1) bits with a default setting of 7 V. If OVP is detected, the FAN54110 terminates charging functionality if charging is active when OVP is detected. The FAN54110 interrupts the host when the OVP event occurs and sets the OVP FLAG bit.

#### **Dynamic Input Voltage Control (DIVC)**

 $V_{BUS}$  is typically 5 V +5% / -10%, depending on the charging current. If the FAN54110 is programmed to a higher current than the charger can support, a regulation control actively regulates the charging current to maintain at least 4.32V (typical) on VBUS. This level is controlled via the VBUS\_REF (Reg02h[3:2]) bits. The FAN54110 reduces the charging current to ensure  $V_{BUS}$  is maintained above the  $V_{BUS\_REF}$  setting. The DIVC regulation loop is enabled by default and disabled with the VBUS\_REG (Reg01h[5]) bit.

If DIVC is disabled, the charging cycle stops when  $V_{\text{BUS}}$  falls below the  $V_{\text{BUS}}$  valid falling threshold ( $V_{\text{INMIN2}}$ ) or below  $V_{\text{BAT}}$ . Charging remains stopped until  $V_{\text{BUS}}$  rises above the rising  $V_{\text{BUS}}$  valid threshold ( $V_{\text{INMIN1}}$ ) and stays above this threshold.

#### Thermal Regulation and Shutdown

The thermal regulation loop is enabled if the junction temperature reaches the threshold defined by the  $T_{\text{CF}}$  (Reg02h[5:4]) bits. When  $T_{\text{CF}}$  is reached, the FAN54110 reduces the charging current to 90 mA until the junction temperature falls below  $T_{\text{CF}}$ . Charge current is then incremented in 1 ms steps until the lochrighed level is reached. This algorithm allows for the fastest recovery from a thermal regulation event while averaging a current that keeps the temperature below  $T_{\text{CF}}$ .

The FAN54110 terminates charging completely if the junction temperature exceeds  $T_{\text{SHUTDWN}}$  (145°C).

In both cases, the temperature event is indicated via the TREG\_FLAG and TSD\_FLAG bits in the FAULT\_INTERRUPT (Reg05h) register. Recovery from either event is indicated via the OT\_RECOV bit in the same register.

Additional  $\theta_{JA}$  data points, measured using the FAN54110 evaluation board, are given in the table below (measured with T<sub>A</sub>=25°C). Note that as power dissipation increases, the effective  $\theta_{JA}$  decreases due to the larger difference between the die temperature and ambient.

Table 1. Evaluation Board Measured θ. ΙΑ

Power (W)	$\Theta_{JA}$
0. 504	54°C/W
0. 844	50°C/W
1. 506	46°C/W

#### **Production Test Mode**

Production Test Mode (PTM) provides power for the system from the USB port. This eliminates the burden of having an attached battery during production line testing.

PTM is enabled when the PTM\_EN bit is HIGH and when the battery is absent (NOBAT (Reg05h[0])=1). In PTM, Q1 (see Figure 2) is turned on, but it is current limited to about 2.5 A.  $V_{BAT}$  is initially regulated to the default  $V_{OREG}$  setting of 3.54 V in PTM. However, VBAT can be programmed to output any  $V_{OREG}$  from 3.38 V to 4.44 V, as specified in the VOREG (Reg04h[5:0]) bits.

Care should be taken to limit the RMS current in PTM Mode. Thermal regulation ( $T_{\text{CF}}$ ) and thermal shutdown are enabled in PTM.

# **Charging Status and Interrupt Reporting**

The STAT and POK\_B pins are used to indicate to the host the presence or absence of a valid charging source, charging status, as well as fault status.

The FAULT\_INTERRUPT (Reg05h[7:0]) and STATUS\_INTERRUPT (Reg07h[7:5]) bits have associated MASK bits and there is a general INTERRUPT (Reg01h[0]) bit. This bit is set when any interrupt occurs, even if the occurring fault is masked. While this bit is set to 1, all subsequent STAT pulses are prevented. Reading this register clears the bit.

The FAULT\_INTERRUPT and STATUS\_INTERRUPT registers and the INTERRUPT (Reg01h[0]) bit should be read and cleared on every STAT pin rising edge and POK\_B pin falling edge to ensure that all faults, masked or otherwise, as well as adapter presence changes are immediately available to the host.

#### POK\_B Pin

The POK\_B pin is used to indicate the presence or absence of a valid charging source to the host processor.

Table 2. POK\_B Pin State

POK_B	Charging Source
HIGH	absent or not valid
LOW	VINMIN(1) <vbus<vbusovp< td=""></vbus<vbusovp<>

#### **STAT Pin**

The STAT pin is used to indicate charging status, as well as to signal the host processor of a change in the status of the IC or system.

The static state of the STAT pin is determined by whether the IC is charging a battery:

Table 3. STAT Pin Static State

CHARGER	NOBAT (Reg05h[0])	STAT Pin
ON	0	LOW
OFF	X	HIGH
Х	1	HIGH

The STAT pin emits a 128  $\mu$ s LOW pulse whenever an unmasked interrupt event occurs and the INTERRUPT (Reg01h[0]) bit is reset to "0".

Any interrupt pulse that occurs while STAT is statically LOW is preceded by 128  $\mu s$  of STAT HIGH, as shown below.

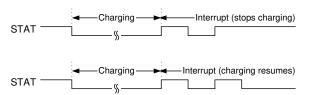


Figure 22. STAT Interrupt Pulse Behavior

#### Masking the STAT Pin Interrupt

The FAULT\_INTERRUPT and STATUS\_INTERRUPT register bits have associated MASK bits located in Reg06h[7:0] and Reg07h[3:1] that will mask STAT pin pulses.

When a mask bit is set and an event occurs:

- The associated FAULT\_INTERRUPT or STATUS\_INTERRUPT bit is set
- The INTERRUPT bit is set
- The STAT pin will not pulse

#### INTERRUPT (Reg01h[0]) Bit

When bits in the FAULT\_INTERRUPT and STATUS\_INTERRUPT register are set, the INTERRUPT (Reg01h[0]) bit is set before the falling edge of STAT.

If additional interrupt conditions occur before the host clears the INTERRUPT bit by reading Reg01h, the STAT pin does not pulse.

#### I<sup>2</sup>C Interface

The serial interface is compatible with Standard Mode and Fast Mode I<sup>2</sup>C bus specifications. The SCL line is an input and the SDA line is a bi-directional open-drain output; it can only pull down the bus when active. The SDA line only pulls LOW during data reads and when signaling ACK. All data is shifted in MSB (bit 7) first.

#### **Slave Address**

Table 4. I<sup>2</sup>C Slave Address Byte

7	6	5	4	3	2	1	0
1	1	0	1	0	1	1	R/W

In hex notation, the slave address assumes a 0 LSB. The hex slave address for the FAN54110 is D6.

#### **Bus Timing**

As shown below, data is normally transferred when SCL is LOW. Data is clocked in on the rising edge of SCL. Typically, data transitions at or shortly after the falling edge of SCL to allow ample time for the data to set up before the next SCL rising edge.

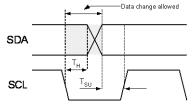
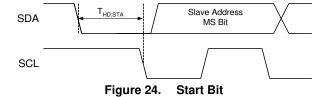
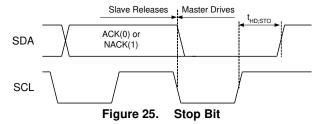


Figure 23. Data Transfer Timing

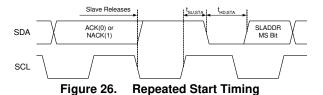
Each bus transaction begins and ends with SDA and SCL HIGH. A transaction begins with a START condition, which is defined as SDA transitioning from 1 to 0 with SCL HIGH, as shown below.



A transaction ends with a STOP condition, which is defined as SDA transitioning from 0 to 1 with SCL HIGH, as shown in Figure 25.



During a read from the FAN54110, the master issues a Repeated Start after sending the register address and before resending the slave address. The Repeated Start is a 1-to-0 transition on SDA while SCL is HIGH, as shown below.



#### **Read and Write Transactions**

The figures below outline the sequences for data read and write. Bus control is signified by the shading of the packet,

defined as Master Drives Bus and All addresses and data are MSB first.

Table 5. Bit Definitions for Write and Read Transactions

Symbol	Definition
S	START, see Figure 24.
А	ACK. The slave drives SDA to 0 to acknowledge the preceding packet.
Ā	NACK. The slave sends a 1 to NACK the preceding packet.
R	Repeated START, see Figure 26
Р	STOP, see Figure 25

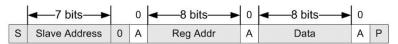


Figure 27. Write Transaction



Figure 28. Read Transaction

# **Register Descriptions**

## Table 6. Register Bit Definitions

Default values are in bold text with VBUS removed and VBAT=3.8V.

Bit	Name	Туре	Description					
IC_INF	<b>-</b> 0	Registe	r Address: 00h	Default= 100X XXXX (XXh)				
7:5	VENDOR	R	100: Identifies ON Semiconductor as the supplier					
4:3	PN	R	Part number bits, see the Ordering Info on page 2					
2:0	REV	R	C Revision. Revision is 1.X, where X is the decimal of these 3 bits					

CHAR	RGE_CTRL1	Registe	er Address	s: 01h	Default=0011 0010 (32h)					
7	RESET	W	go to into	Setting this bit to 1 resets all registers to default values and deactivates t <sub>32S</sub> , causing the part to go to into IDLE State until the next I <sup>2</sup> C write reactivates t <sub>32S</sub> .  This bit returns 0 when read.						
6	HZ_MODE	R/W		rging is enabled. rging is disabled.						
5	VBUS_REG	R/W		s regulation loop disabled. s regulation loop enabled.						
4	VBUS_LOOP	R		200 - 31 - 11 - 11 - 11 - 11 - 11 - 11 -						
3	Reserved	R	This bit re	eturns 0 when read.						
				until the fault clears.	SOVP fault is enunciated and the charger is					
			[2:1]	V <sub>BUSOVP</sub> Threshold						
2:1	V <sub>BUSOVP</sub>	R/W	00	6.5						
			01	7.0						
			10	7.5						
			11	8.0						
0	INTERRUPT	RC	A 1 indicates that a fault has occurred. See the Charging Status and Interrupt Reporting section for details.  While this bit is set to 1, all subsequent STAT pulses are prevented. Reading this register clears the bit.							

CHAR	GE_CTRL2	Registe	er Address	: 02h		Default=0010 0111 (27h)					
7	PTM_EN	R/W	1: Produ								
6	Reserved	R	This bit re	turns 0 w	hen read.						
					hold at which the current is n and Shutdown section fo	reduced to allow the device to cool. See the r details.					
			Table 8.	Temp	erature Threshold Sett	tings					
			DEC	BIN	T <sub>CF</sub>						
5:4	T <sub>CF</sub>	R/W	0	00	70						
			1	01	85						
				2	10	100					
			3	11	120						
			Sets the V <sub>BUS_REF</sub> threshold.								
			Table 9.	V <sub>BUS_F</sub>	REF Threshold						
			DEC	BIN	V <sub>BUS_REF</sub>						
3:2	VBUS_REF	R/W	0	00	4.22						
			1	01	4.32						
			2	10	4.37						
			3	11	4.46						
1	VRCH_DIS	R/W	<ul> <li>0: Charging re-starts if V<sub>BAT</sub> &lt; V<sub>OREG</sub>-V<sub>RCH</sub>.</li> <li>1: Charging does not re-start automatically if V<sub>BAT</sub> drops.</li> </ul>								
0	ITERM_DIS	R/W	O: Charging terminates at the programmed I <sub>TERM</sub> level.  1: Charging does not terminate at the programmed I <sub>TERM</sub> level.								

BAT		Registe	r Address	s: 03h		Default=0010 0110 (26h)
			consume	d by the 3		nt drawn from VBUS during charging. Current es the current available to charge the battery.
			DEC	BIN	I <sub>OCHARGE</sub> (mA)	$\neg$
			0	0000	100	
			1	0001	300	
			2	0010	350	
			3	0011	400	
			4	0100	450	
			5	0101	500	
7:4	IOCHARGE	R/W	6	0110	550	
			7	0111	600	
			8	1000	650	
			9	1001	700	
			10	1010	750	
			11	1011	800	
			12	1100	850	
			13	1101	900	
			14	1110	950	
			15	1111	1000	
			Table 1	I. ITERN	// Settings	
			DEC	BIN	ITERM (mA)	
			0	0000	20	
			1	0001	30	
			2	0010	40	
			3	0011	50	
			4	0100	60	
			5	0101	70	
3:0	ITERM	RΛΛΙ	6	0110	80	
5.0	ITERM	R/W	7	0111	90	
			8	1000	100	
			9	1001	110	
			10	1010	120	
			11	1011	130	
			12	1100	140	
			13	1101	150	
			14	1110	160	
			15	1111	170	

DREG	ì	Registe	er Address:	04h			De	efault	=0000 1000	(08h)	
7:6	Reserved	R	These bits	return 0 whe	en read.						
			Table 12.	OREG Se	ettings						
			DEC	BIN	HEX	V <sub>OREG</sub>	D	EC	BIN	HEX	Vore
			0	000000	00	3.38	(	32	100000	20	4.02
			1	000001	01	3.40	(	33	100001	21	4.04
			2	000010	02	3.42	(	34	100010	22	4.06
			3	000011	03	3.44	(	35	100011	23	4.08
			4	000100	04	3.46	(	36	100100	24	4.10
			5	000101	05	3.48	(	37	100101	25	4.12
			6	000110	06	3.50	(	38	100110	26	4.14
			7	000111	07	3.52	(	39	100111	27	4.16
			8	001000	08	3.54	4	40	101000	28	4.18
			9	001001	09	3.56	4	41	101001	29	4.20
			10	001010	0A	3.58	4	42	101010	2A	4.2
			11	001011	0B	3.60	4	43	101011	2B	4.2
			12	001100	0C	3.62	4	14	101100	2C	4.20
			13	001101	0D	3.64	4	45	101101	2D	4.28
5:0	VOREG	R/W	14	001110	0E	3.66	4	46	101110	2E	4.30
0.0	VOITEG	1000	15	001111	0F	3.68	4	47	101111	2F	4.32
			16	010000	10	3.70	4	48	110000	30	4.34
			17	010001	11	3.72	4	49	110001	31	4.30
			18	010010	12	3.74	į	50	110010	32	4.38
			19	010011	13	3.76	į	51	110011	33	4.40
			20	010100	14	3.78	į	52	110100	34	4.42
			21	010101	15	3.80	į	53	110101	35	4.44
			22	010110	16	3.82	į	54	110110	36	4.44
			23	010111	17	3.84	į	55	110111	37	4.44
			24	011000	18	3.86	į	56	111000	38	4.44
			25	011001	19	3.88	į	57	111001	39	4.44
			26	011010	1A	3.90	į	58	111010	3A	4.44
			27	011011	1B	3.92	į	59	111011	3B	4.44
			28	011100	1C	3.94	(	30	111100	3C	4.44
			29	011101	1D	3.96	(	31	111101	3D	4.44
			30	011110	1E	3.98	(	62	111110	3E	4.44
			31	011111	1F	4.00	(	63	111111	3F	4.44

FAUL	T_INTERRUPT	Registe	r Addres	s: 05h	Default=0000 0000 (00h)		
			Items in other inte	A 1 for a given bit indicates that a specific fault has occurred as described in the table be tems in blue are transient conditions, whose bits are cleared when this register is read. other interrupts herein are not cleared unless the underlying condition has been removed. See the Charging Status and Interrupt Reporting section for details.			
			Table 13	3. Charger Inter	rupt Conditions		
			Bit #	FLAG	Interrupt		
			7	TSD_FLAG	Thermal shutdown (T <sub>J</sub> > 145°C).		
7:0	FAULT	R	R	R	6	OVP_FLAG	VBUS OVP (over-voltage shutdown).
	_INTERRUPT		5	TREG_FLAG	Charger thermal regulation is active.		
			4	TC_TO	T32Sec timer has timed out.		
		3 2 1	DBP_TO	Dead-Battery (DBP) timer (T30) has timed out.			
			2	OT_RECOV	Die temperature has fallen below 120°C.		
			1	OVP_RECOV	VBUS OVP recovery has occurred.		
			0	NOBAT	Battery absence was detected either at VBUS POR or after Charge Termination.		

FAUL	FAULT_MASK Register			: 06h	Default=0000 0000 (00h)
		IN <sup>-</sup> wri	INTERRU written.	PT (Reg01h[0]) bi	In interrupt pulse from being generated on the STAT pin. The it and corresponding FAULT_INTERRUPT register bit are still Interrupt Reporting section for details.
			Bit #	FLAG	Interrupt
			7	TSD_FLAG_M	Mask thermal shutdown (T <sub>J</sub> > 145°C).
7:0	MASK	R/W	6	OVP_FLAG_M	Mask VBUS OVP (over-voltage shutdown).
7.0			5	TREG_FLAG_M	Mask charger thermal regulation.
			4	TC_TO_M	Mask T32Sec timer time out.
			3	DBP_TO_M	Mask Dead-Battery (DBP) timer (t30) time out.
			2	OT_RECOV_M	Mask Die temperature recovery.
			1	OVP_RECOV_M	Mask VBUS OVP recovery.
			0	NOBAT_M	Mask battery absence detection.

STATI	US_INTERRUPT	Γ Defa	ult=0100 (	0000 (40h)		Register Address: 07h	
			other inter	rrupts herein are no Charging Status and	ot cleared unless the state of	bits are cleared when this register is read. The ne underlying condition has been removed. ng section for details.	
			Table 14	. VBUS Interrup	t Conditions		
			Bit #	FLAG		Interrupt Generated	
7:5	7:5 VBUS_STAT	R	7	VBUS_CON	0 when VBUS is VBUS_CON does	US>VIIN(MIN)1 at VBUS POR from VBUS Insertion. disconnected. s not de-assert when a VBUS_OVP condition S validation is successful.	
			6	POK_B	State of the POK	_B pin	
			5	VALIDATION FAIL		S validation is attempted and failed. After a lidation is attempted every two seconds.	
4	Reserved	R	This bit re	turns 0 when read.			
			INTERRU	PT (Reg01h[0]) bit	and corresponding	from being generated on the STAT pin. The g VBUS_STAT bit are still written.  ng section for details.	
			Table 15	. VBUS Interru	pt Mask Bits		
3:1	VBUS_MASK	R/W	Bit #	Ma	sk		
			3	VBUS_CON MAS	K		
			2	POK_B MASK			
			1	VALIDATION FAII	L MASK		
0	Reserved	R	This bit re	This bit returns 0 when read.			

TMR_	TMR_RST		r Address: 08h	Default=0000 0000 (00h)
7	TMR_RST	W	Setting this bit to 1 resets the $t_{32s}$ time the $l^2C$ host.  This bit returns 0 when read	r, allowing the IC to continue charging under control of
6:0	Reserved	R	These bits return 0 when read.	

MONITOR0		Registe	er Address: 10h Default=1000 0010 (82h)		
7	ITERM_CMP	R	0: I <sub>BAT</sub> < I <sub>TERM</sub> reference 1: I <sub>BAT</sub> > I <sub>TERM</sub> reference		
6	VBUS_VBAT	R	0: VBUS < VBAT 1: VBUS > VBAT		
5	VSHORT	R	<ul> <li>0: VBAT &gt; VSHORT or IC is not charging.</li> <li>1: VBAT &lt; VSHORT and IC is charging.</li> </ul>		
4	DIS_LEVEL	R	O: DIS pin is LOW. This bit always reads 0 when VBUS is disconnected.  1: DIS pin is HIGH.		
3:2	Reserved	R	This bit returns 0 when read.		
1	ICHG	R	ICHG loop is controlling the charge current.     ICHG loop is not limiting the charge current.		
0	CV	R	O: Charger is not in Constant Voltage (CV) Mode. Charger is either off or another loop (VBUS or ICHG) is limiting charge current.  1: Charger is on and in Constant Voltage (CV) Mode.		

# **PCB Layout Recommendations**

Bypass capacitors should be placed as close to the IC as possible. All power and ground pins should be routed to their bypass capacitors using top copper. Copper area connecting to the IC should be maximized to improve thermal performance.

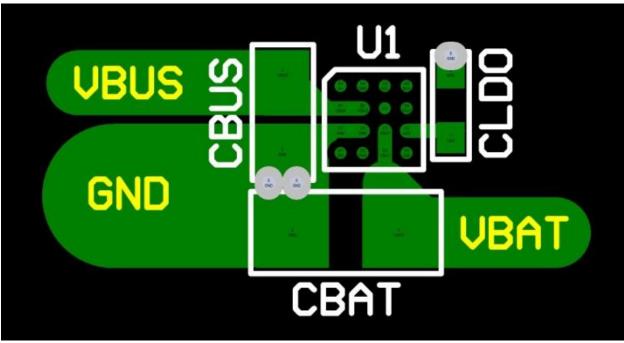
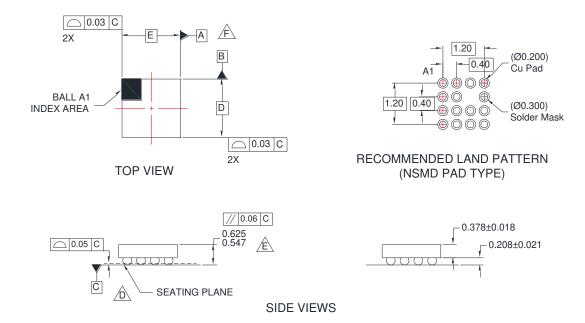
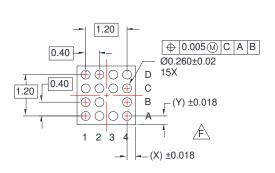


Figure 29. Recommended PCB Layout

# **Physical Dimensions**





**BOTTOM VIEW** 

#### **NOTES**

- A. NO JEDEC REGISTRATION APPLIES.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCE PER ASMEY14.5M, 1994.
- D. DATUM C IS DEFINED BY THE SPHERICAL CROWNS OF THE BALLS.
- PACKAGE NOMINAL HEIGHT IS 586 ± 39 MICRONS (547-625 MICRONS).
- F. FOR DIMENSIONS D, E, X, AND Y SEE PRODUCT DATASHEET.
- G. DRAWING FILNAME: MKT-UC015AArev1.

Figure 30. 15-Ball WLCSP, 0. 4 mm Pitch, 250 µm Balls

# **Product-Specific Dimensions**

D	E	X	Υ
1. 560 ±0.030	1. 560 ± 0.030	0.180	0.180

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